

# **PMBFJ174; PMBFJ175;** PMBFJ176; PMBFJ177 P-channel silicon field-effect transistors Rev. 3.0 – 24 January 2020

Product data sheet

#### **Product profile** 1

## 1.1 General description

Silicon symmetrical p-channel junction FETs in plastic microminiature SOT23 envelopes. They are intended for application with analogue switches, choppers, commutators etc. using SMD technology. A special feature is the interchangeability of the drain and source connections.

## 1.2 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage		30	-	30	V
V <sub>GSo</sub>	gate-source voltage		-	-	30	V
-I <sub>G</sub>	gate current		-	-	50	mA
P <sub>tot</sub>	total power dissipation	up to $T_{amb}$ = 25 ° C	-	-	300	mW
-I <sub>DSS</sub>	drain current	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0				
		PMBFJ174	20	-	135	mA
		PMBFJ175	7	-	70	mA
		PMBFJ176	2	-	35	mA
		PMBFJ177	1.5	-	20	mA
$R_{DSon}$	drain-source ON-	-V <sub>DS</sub> = 0.1 V; V <sub>GS</sub> = 0				
	resistance	PMBFJ174	-	-	85	Ω
		PMBFJ175	-	-	125	Ω
		PMBFJ176	-	-	250	Ω
		PMBFJ177	-	-	300	Ω

#### Table 1. Quick reference data



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# 2 Pinning information

Table 2. Pinn	ing		
Pin	Description <sup>[1]</sup>	Simplified outline	Symbol
1	drain		
2	source		3 → 2
3	gate		sym053

[1] Drain and source are interchangeable.

# **3** Ordering information

#### Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PMBFJ174	-	plastic surface mounted package; 3 leads	SOT23				
PMBFJ175							
PMBFJ176	_						
PMBFJ177							

# 4 Marking

Table 4. Marking	
Type number	Marking code <sup>[1]</sup>
PMBFJ174	*6X
PMBFJ175	*6W
PMBFJ176	*6S
PMBFJ177	*6Y

[1] \* = manufacturing site

# 5 Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage		30	30	V
V <sub>GSO</sub>	gate-source voltage		-	30	V
V <sub>GDO</sub>	gate-drain voltage		-	30	V

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Symbol	Parameter	Conditions		Min	Max	Unit
-I <sub>G</sub>	gate current (DC)			-	50	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 ° C	[1]	-	300	mW
T <sub>stg</sub>	storage temperature range			-65	150	° C
Tj	junction temperature			-	150	°C

[1] Mounted on a ceramic substrate, 8 mm × 10 mm × 0.7 mm.

# **6** Thermal characteristics

#### Table 6. Thermal characteristics

 $T_j = P \left( R_{th(j-t)} + R_{th(t-s)} + R_{th(s-a)} \right) + T_{amb}.$ 

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-a)</sub>	junction to ambient in free air thermal resistance		430	K/W

# 7 Static characteristics

#### Table 7. Static characteristics

 $T_i = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
I <sub>GSS</sub>	gate cut-off current									
	PMBFJ174	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V	-	-	1	nA				
	PMBFJ175	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V	-	-	1	nA				
	PMBFJ176	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V	-	-	1	nA				
	PMBFJ177	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V	-	-	1	nA				
-I <sub>DSX</sub>	drain cut-off current	~								
	PMBFJ174	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V	-	-	1	nA				
	PMBFJ175	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V	-	-	1	nA				
	PMBFJ176	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V	-	-	1	nA				
	PMBFJ177	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V	-	-	1	nA				
-I <sub>DSS</sub>	drain current									
	PMBFJ174	V <sub>DS</sub> = -15 V; V <sub>GS</sub> = 0 V	20	-	135	mA				
	PMBFJ175	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V	7	-	70	mA				
	PMBFJ176	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V	2	-	35	mA				
	PMBFJ177	-V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V	1.5	-	20	mA				
V <sub>(BR)GSS</sub>	gate-source breakdown voltage									
	PMBFJ174	I <sub>G</sub> = 1 μA; V <sub>DS</sub> = 0 V	-	-	30	V				
	PMBFJ175	I <sub>G</sub> = 1 μA; V <sub>DS</sub> = 0 V	-	-	30	V				
	PMBFJ176	I <sub>G</sub> = 1 μA; V <sub>DS</sub> = 0 V	-	-	30	V				
	PMBFJ177	I <sub>G</sub> = 1 μA; V <sub>DS</sub> = 0 V	-	-	30	V				

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit			
V <sub>GSoff</sub>	gate-source cut-off voltage								
	PMBFJ174	-I <sub>D</sub> = 10 nA; V <sub>DS</sub> = -15 V	5	-	10	V			
	PMBFJ175	-I <sub>D</sub> = 10 nA; V <sub>DS</sub> = -15 V	3	-	6	V			
	PMBFJ176	-I <sub>D</sub> = 10 nA; V <sub>DS</sub> = -15 V	1	-	4	V			
	PMBFJ177	-I <sub>D</sub> = 10 nA; V <sub>DS</sub> = -15 V	0.8	-	2.25	V			
R <sub>DSon</sub>	drain-source on resistance								
	PMBFJ174	-V <sub>DS</sub> = 0.1 V; V <sub>GS</sub> = 0 V	-	-	85	Ω			
	PMBFJ175	-V <sub>DS</sub> = 0.1 V; V <sub>GS</sub> = 0 V	-	-	125	Ω			
	PMBFJ176	-V <sub>DS</sub> = 0.1 V; V <sub>GS</sub> = 0 V	-	-	250	Ω			
	PMBFJ177	-V <sub>DS</sub> = 0.1 V; V <sub>GS</sub> = 0 V	-	-	300	Ω			

# 8 Dynamic characteristics

#### Table 8. Dynamic characteristics

 $T_i = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; f = 1 MHz		-	8	-	pF
		$V_{DS}$ = 0 V; $V_{GS}$ = 0 V; f = 1 MHz		-	30	-	pF
C <sub>rs</sub>	feedback capacitance	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; f = 1 MHz		-	4	-	pF
Switching	times; see Figure 1and F	Figure 2, Test conditions for switching times are as f	follows	s: <sup>[1]</sup>			-
t <sub>d</sub>	delay time						
	PMBFJ174			-	2	-	ns
	PMBFJ175			-	5	-	ns
	PMBFJ176			-	15	-	ns
	PMBFJ177			-	20	-	ns
t <sub>r</sub>	rise time						
	PMBFJ174			-	5	-	ns
	PMBFJ175			-	10	-	ns
	PMBFJ176			-	20	-	ns
	PMBFJ177			-	25	-	ns
t <sub>on</sub>	turn-on time						
	PMBFJ174			-	7	-	ns
	PMBFJ175			-	15	-	ns
	PMBFJ176			-	35	-	ns
	PMBFJ177			-	45	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t <sub>s</sub>	storage temperature					
	PMBFJ174		-	5	-	ns
	PMBFJ175		-	10	-	ns
	PMBFJ176		-	15	-	ns
	PMBFJ177		-	20	-	ns
t <sub>f</sub>	fall time					
	PMBFJ174		-	10	-	ns
	PMBFJ175		-	20	-	ns
	PMBFJ176		-	20	-	ns
	PMBFJ177		-	25	-	ns
t <sub>off</sub>	turn-off time					
	PMBFJ174		-	6	-	ns
	PMBFJ175		-	6	-	ns
	PMBFJ176		-	6	-	ns
	PMBFJ177		-	6	-	ns



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#### P-channel silicon field-effect transistors

# 9 Package outline



Figure 3. Package outline.

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# **10 Revision history**

Revision history					
Revision number	Date	Description			
3.0	20200124	Product data sheet			
modification	adapted the notation of the manufacturing code				
2.0	19950401	product data sheet			
1.0		Initial version of the document			

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# **11 Legal information**

## 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
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